

# ON Semiconductor

## Is Now

# onsemi™

To learn more about onsemi™, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

---

**onsemi** and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

# NYC008-6JG

## Sensitive Gate Silicon Controlled Rectifiers

### Reverse Blocking Thyristors

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

#### Features

- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 V
- On-State Current Rating of 0.8 A RMS at 80°C
- High Surge Current Capability – 10 A
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to  $dV/dt$  – 50 V/ $\mu$ sec Minimum at 110°C
- Glass-Passivated Surface for Reliability and Uniformity
- These are Pb-Free Devices



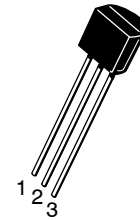
ON Semiconductor®

<http://onsemi.com>

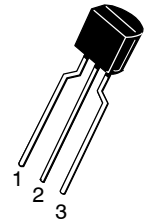
**SCRs**  
**0.8 A RMS**  
**600 V**



TO-92  
CASE 29  
STYLE 10

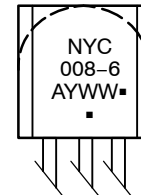


STRAIGHT LEAD  
BULK PACK



BENT LEAD  
TAPE & REEL  
AMMO PACK

#### MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### PIN ASSIGNMENT

1	Cathode
2	Gate
3	Anode

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NYC008-6JG

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Notes 1 and 2) (T <sub>J</sub> = -40 to 110°C, Sine Wave, 50 to 60 Hz; R <sub>GK</sub> = 1 kΩ)	V <sub>DRM</sub> , V <sub>RRM</sub>	600	V
On-State RMS Current, (T <sub>C</sub> = 80°C) 180° Conduction Angles	I <sub>T(RMS)</sub>	0.8	A
Peak Non-Repetitive Surge Current, (1/2 Cycle, Sine Wave, 60 Hz, T <sub>J</sub> = 25°C)	I <sub>TSM</sub>	10	A
Circuit Fusing Consideration, (t = 8.3 ms)	I <sup>2</sup> t	0.415	A <sup>2</sup> s
Forward Peak Gate Power, (T <sub>A</sub> = 25°C, Pulse Width ≤ 1.0 μs)	P <sub>GM</sub>	0.1	W
Forward Average Gate Power, (T <sub>A</sub> = 25°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.10	W
Forward Peak Gate Current, (T <sub>A</sub> = 25°C, Pulse Width ≤ 1.0 μs)	I <sub>GM</sub>	1.0	A
Reverse Peak Gate Voltage, (T <sub>A</sub> = 25°C, Pulse Width ≤ 1.0 μs)	V <sub>GRM</sub>	5.0	V
Operating Junction Temperature Range @ Rate V <sub>RRM</sub> and V <sub>DRM</sub>	T <sub>J</sub>	-40 to 110	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- See ordering information for exact device number options.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	R <sub>θJC</sub> R <sub>θJA</sub>	75 200	°C/W
Lead Solder Temperature ( < 1/16" from case, 10 secs max)	T <sub>L</sub>	260	°C

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

## OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current (Note 3) (V <sub>D</sub> = Rated V <sub>DRM</sub> and V <sub>RRM</sub> ; R <sub>GK</sub> = 1 kΩ)	I <sub>DRM</sub> , I <sub>RRM</sub>	-	10 100	μA

## ON CHARACTERISTICS

Peak Forward On-State Voltage* (I <sub>TM</sub> = 1.0 A Peak @ T <sub>A</sub> = 25°C)	V <sub>TM</sub>	-	1.7	V
Gate Trigger Current (Note 4) T <sub>C</sub> = 25°C (V <sub>AK</sub> = 7.0 Vdc, R <sub>L</sub> = 100 Ω)	I <sub>GT</sub>	-	200	μA
Holding Current (Note 3) T <sub>C</sub> = 25°C (V <sub>AK</sub> = 7.0 Vdc, Initiating Current = 20 mA, R <sub>GK</sub> = 1 kΩ) T <sub>C</sub> = -40°C	I <sub>H</sub>	-	5.0 10	mA
Latch Current (Note 4) T <sub>C</sub> = 25°C (V <sub>AK</sub> = 7.0 V, I <sub>g</sub> = 200 μA) T <sub>C</sub> = -40°C	I <sub>L</sub>	-	10 15	mA
Gate Trigger Voltage (Note 4) T <sub>C</sub> = 25°C (V <sub>AK</sub> = 7.0 Vdc, R <sub>L</sub> = 100 Ω) T <sub>C</sub> = -40°C	V <sub>GT</sub>	-	0.8 1.2	V

## DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, R <sub>GK</sub> = 1 kΩ, T <sub>J</sub> = 110°C)	dV/dt	50	-	V/μs
Critical Rate of Rise of On-State Current (I <sub>PK</sub> = 20 A; P <sub>w</sub> = 10 μsec; diG/dt = 1 A/μsec, I <sub>gt</sub> = 20 mA)	di/dt	-	50	A/μs

\*Indicates Pulse Test: Pulse Width ≤ 1.0 ms, Duty Cycle ≤ 1%.

- R<sub>GK</sub> = 1000 Ω included in measurement.
- Does not include R<sub>GK</sub> in measurement.

Voltage Current Characteristic of SCR

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Off State Reverse Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Peak on State Voltage
$I_H$	Holding Current

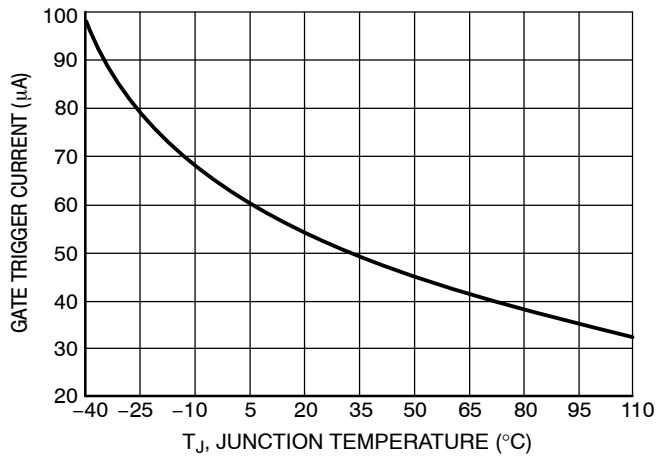
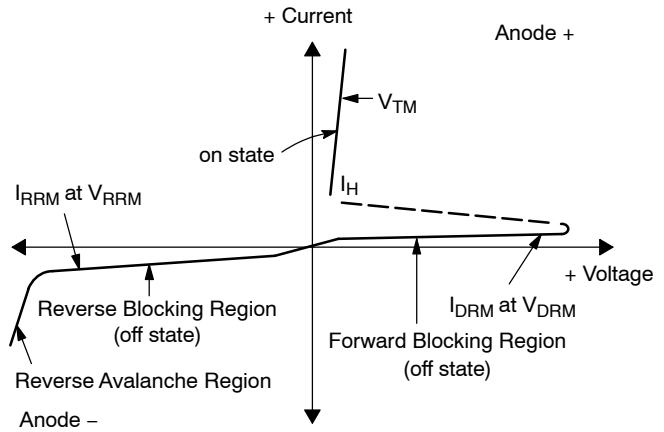


Figure 1. Typical Gate Trigger Current versus Junction Temperature

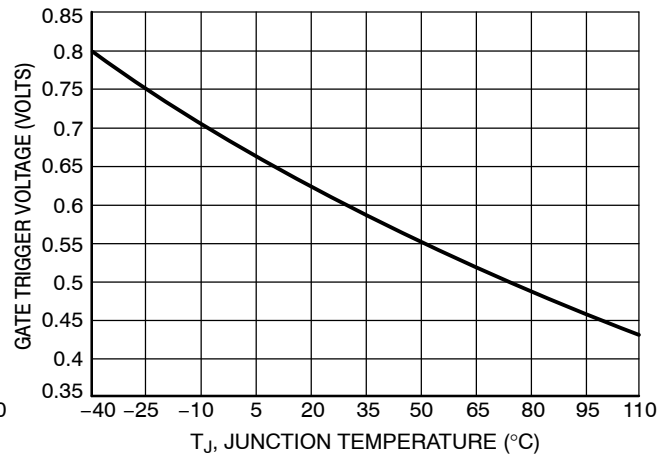
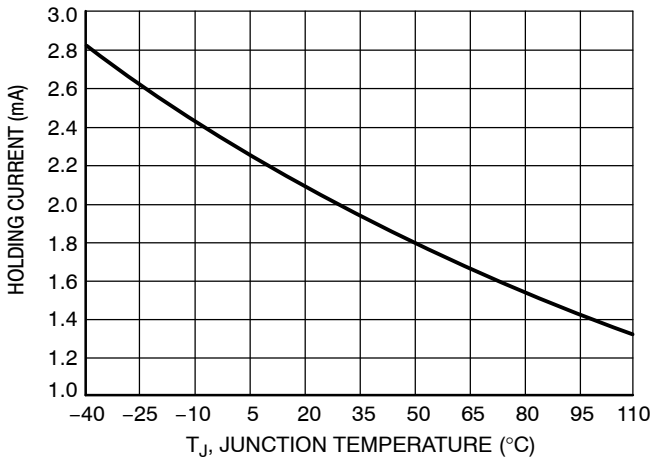
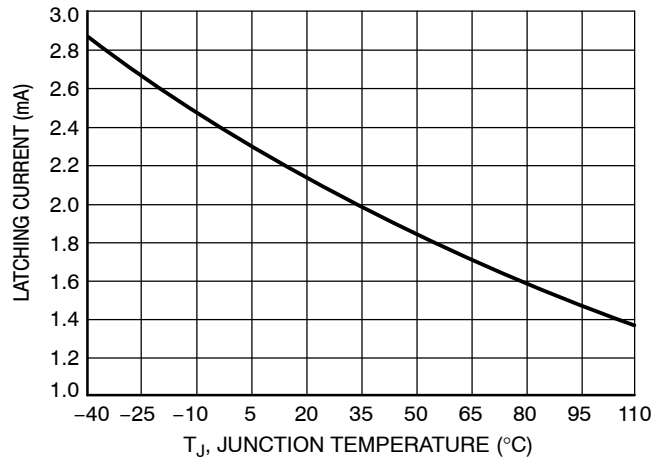


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

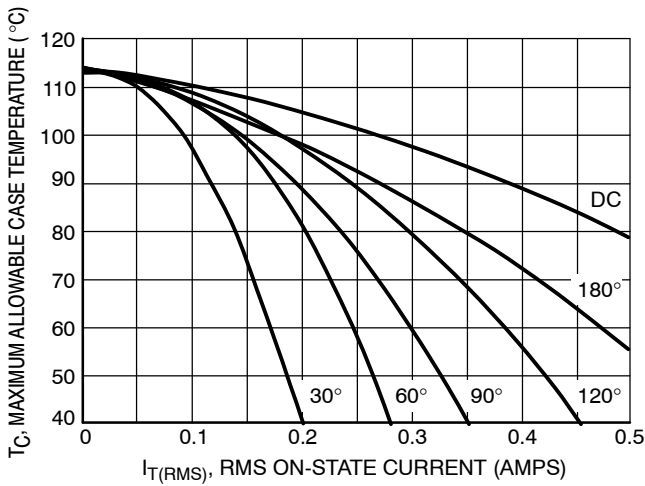
# NYC008-6JG



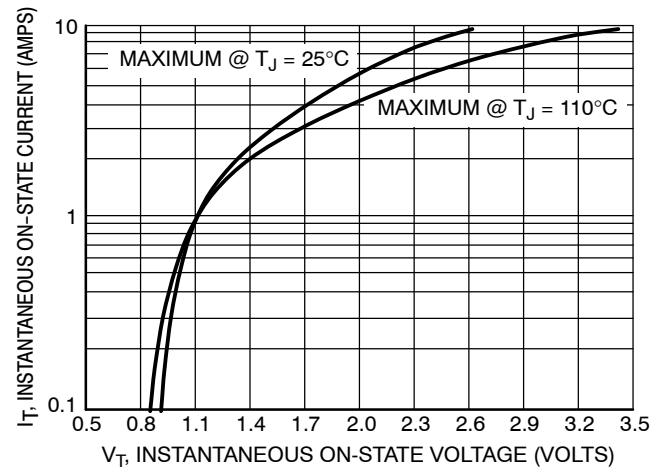
**Figure 3. Typical Holding Current versus Junction Temperature**



**Figure 4. Typical Latching Current versus Junction Temperature**



**Figure 5. Typical RMS Current Derating**



**Figure 6. Typical On-State Characteristics**

# NYC008-6JG

## ORDERING INFORMATION

Device	Package Code	Shipping†
NYC008-6JG	TO-92 (TO-226) (Pb-Free)	5000 Units / Box
NYC008-6JRLRAG		2000 / Tape & Reel
NYC008-6JRLREG		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TO-92 EIA RADIAL TAPE IN BOX OR ON REEL

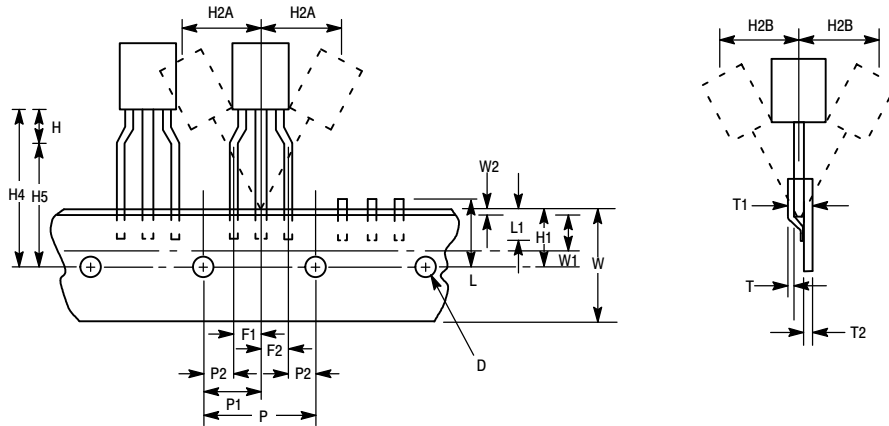


Figure 7. Device Positioning on Tape

Symbol	Item	Specification			
		Inches		Millimeter	
		Min	Max	Min	Max
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8
H	Bottom of Component to Seating Plane	.059	.156	1.5	4.0
H1	Feedhole Location	0.3346	0.3741	8.5	9.5
H2A	Deflection Left or Right	0	0.039	0	1.0
H2B	Deflection Front or Rear	0	0.051	0	1.0
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11
L1	Lead Wire Enclosure	0.09842	—	2.5	—
P	Feedhole Pitch	0.4921	0.5079	12.5	12.9
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95
T	Adhesive Tape Thickness	0.06	0.08	0.15	0.20
T1	Overall Taped Package Thickness	—	0.0567	—	1.44
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65
W	Carrier Strip Width	0.6889	0.7481	17.5	19
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5

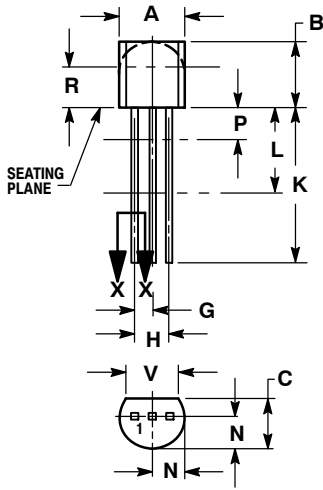
NOTES:

1. Maximum alignment deviation between leads not to be greater than 0.2 mm.
2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
3. Component lead to tape adhesion must meet the pull test requirements.
4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
5. Hold down tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
6. No more than 1 consecutive missing component is permitted.
7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.
8. Splices will not interfere with the sprocket feed holes.

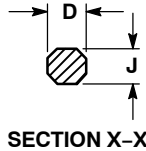
# NYC008-6JG

## PACKAGE DIMENSIONS

### TO-92 (TO-226) CASE 29-11 ISSUE AM



STRAIGHT LEAD  
BULK PACK

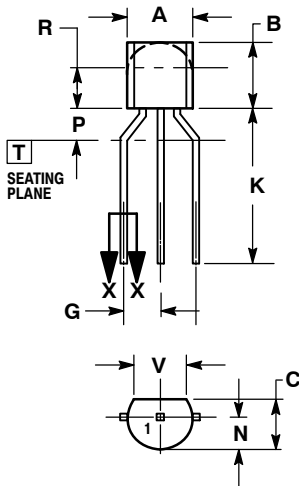


SECTION X-X

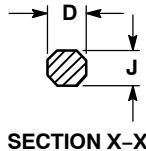
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 10:

1. CATHODE
2. GATE
3. ANODE

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

**LITERATURE FULFILLMENT:**  
Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** orderlit@onsemi.com

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5773-3850

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative